

SuperMOS –TO-252 60V BV_{DSS} , 26m Ω $R_{DS(on)}$, 20A I_D , N-channel MOSFET

1. Description

The ES35N06A is N-Channel enhancement MOS Field Effect Transistor. Uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. Device is suitable for use in DC-DC conversion, power switch and charging circuit. Standard Product ES35N06A is Pb-free.

2. Features

- 60V, $R_{DS(ON)}=26m\Omega(Typ)$, $V_{GS}=10V$
 $R_{DS(ON)}=33m\Omega(Typ)$, $V_{GS}=4.5V$
- Use trench MOSFET technology
- High density cell design for low $R_{DS(on)}$
- Material: Halogen free
- Reliable and rugged
- Avalanche Rated
- Low leakage current

3. Applications


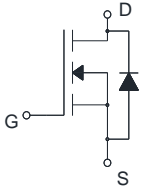
- PWM applications
- Load switch
- Power management in portable/desktop PCs
- DC/DC conversion

100% UIS TESTED!

4. Ordering Information

Part Number	Package	Marking	Material	Packing	Quantity per reel	Flammability Rating	Reel Size
ES35N06A	TO-252	ES35N06A/lot	Halogen free	Tape & Reel	2,500 PCS	UL 94V-0	13 inches

5. Pin Configuration and Functions

Pin	Function	Outline	Circuit Diagram
1	Gate		
3	Source		
2	Drain		

6. Specification

Absolute Maximum Rating & Thermal Characteristics

Ratings at 25 °C ambient temperature unless otherwise specified.

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		BV_{DSS}	60	V
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current	$T_C=25^\circ\text{C}$	I_D	20	A
	$T_C=75^\circ\text{C}$		16	
Maximum Power Dissipation	$T_C=25^\circ\text{C}$	P_D	25	W
	$T_C=75^\circ\text{C}$		15	
Pulsed Drain Current ^a		I_{DM}	80	A
Operating Junction Temperature		T_J	150	$^\circ\text{C}$
Lead Temperature		T_L	260	$^\circ\text{C}$
Storage Temperature Range		T_{stg}	-55 to 150	$^\circ\text{C}$

Thermal resistance ratings

Single Operation					
Parameter		Symbol	Typ	Max	Unit
Junction-to-Case Thermal Resistance	Steady State	$R_{\theta JC}$		5	$^\circ\text{C/W}$

Note:

a: Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

Electrical Characteristics

At TA = 25°C unless otherwise specified

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	60			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=60V, V_{GS}=0V$			1.0	μA
Gate-to-source Leakage Current	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 20V$			± 100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	1.0	1.6	2.5	V
Drain-to-source On-resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=20A$		26	33	m Ω
		$V_{GS}=4.5V, I_D=10A$		33	45	
Forward Trans conductance	g_{FS}	$V_{DS}=5.0V, I_D=20A$			40	S
CHARGES, CAPACITANCES AND GATE RESISTANCE						
Input Capacitance	C_{ISS}	$V_{GS}=0V, f=1MHz,$ $V_{DS}=25V$		1150		pF
Output Capacitance	C_{OSS}			60		
Reverse Transfer Capacitance	C_{RSS}			50		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS}=10V, V_{DS}=30V,$ $I_D=10A$		20		nC
Gate-to-Source Charge	Q_{GS}			4		
Gate-to-Drain Charge	Q_{GD}			5		
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	$t_{d(ON)}$	$V_{GS}=10V, V_{DS}=30V,$ $I_D=20A, R_G=1.8\Omega$		8		ns
Rise Time	t_r			20		
Turn-Off Delay Time	$t_{d(OFF)}$			15		
Fall Time	t_f			25		
BODY DIODE CHARACTERISTICS						
Forward Voltage	V_{SD}	$V_{GS}=0V, I_S=10A$		0.7	1.5	V

7. Typical Characteristic

Figure 1: Output Characteristics

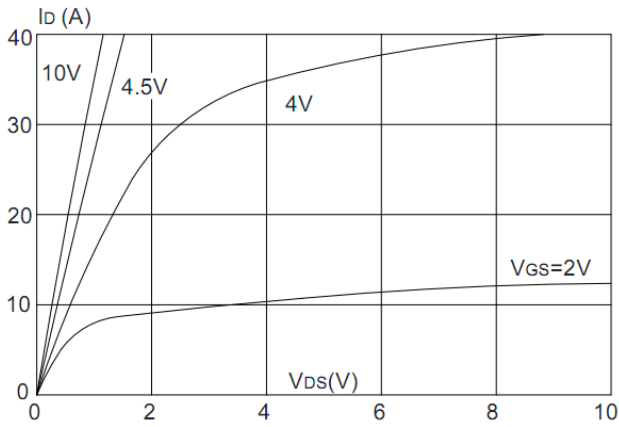


Figure 2: Typical Transfer Characteristics

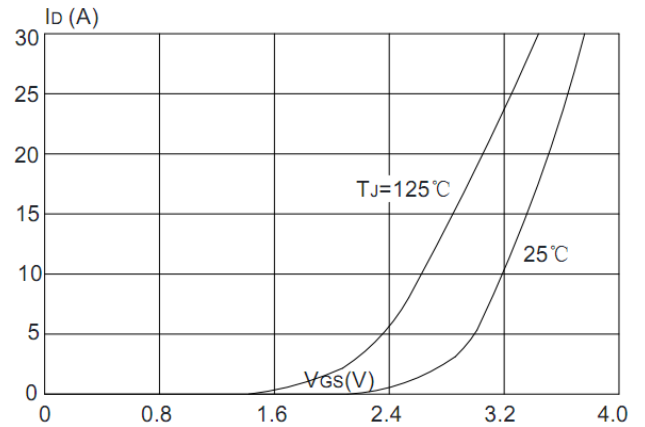


Figure 3: On-resistance vs. Drain Current

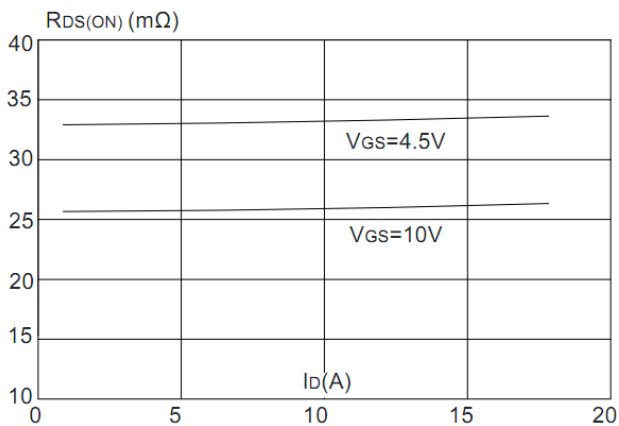


Figure 4: Body Diode Characteristics

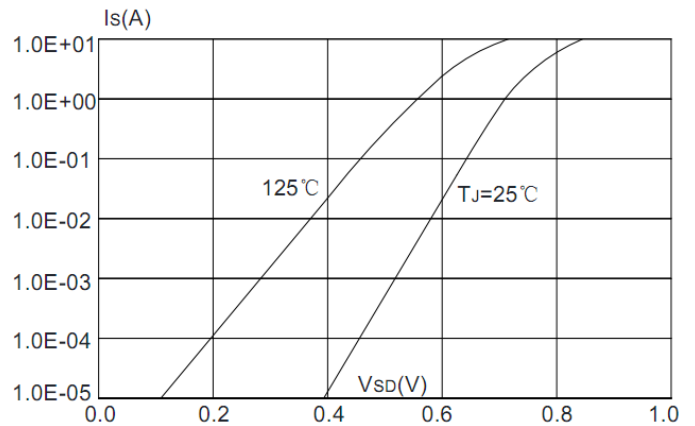


Figure 5: Gate Charge Characteristics

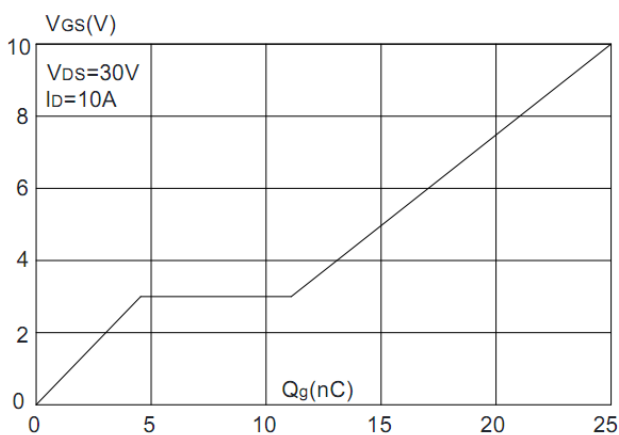


Figure 6: Capacitance Characteristics

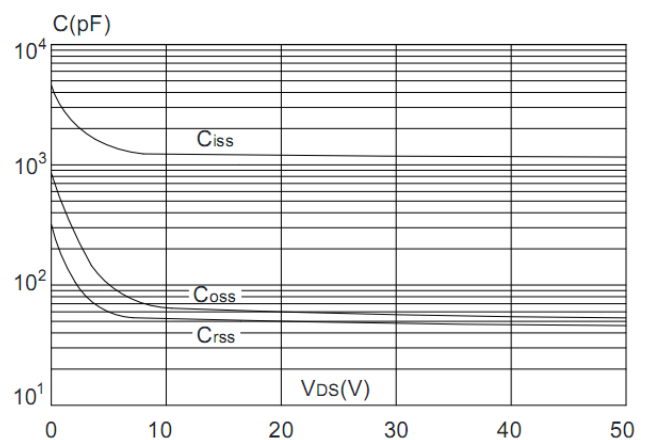


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

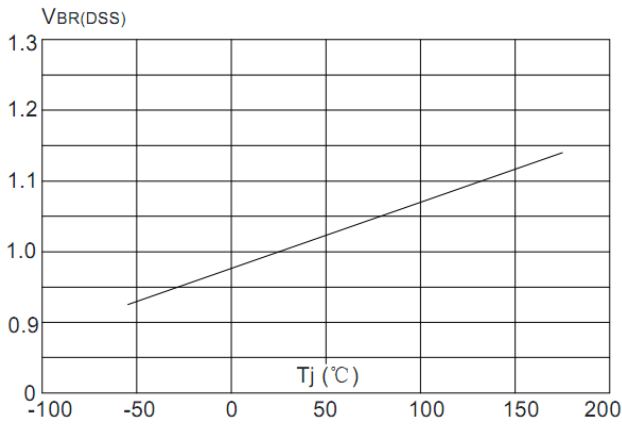


Figure 8: Normalized on Resistance vs. Junction Temperature

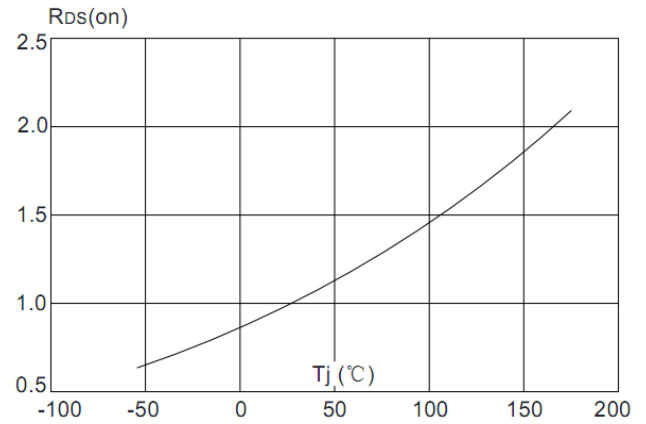


Figure 9: Maximum Safe Operating Area

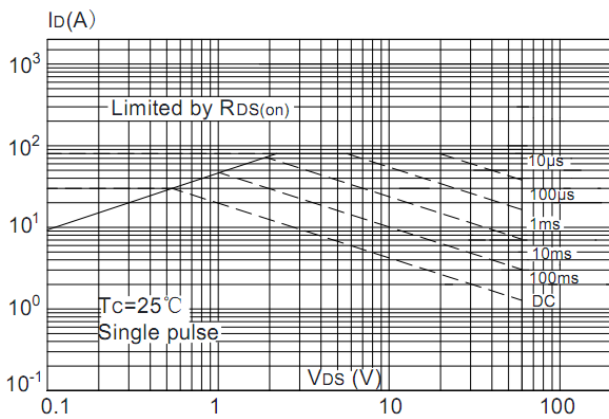


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

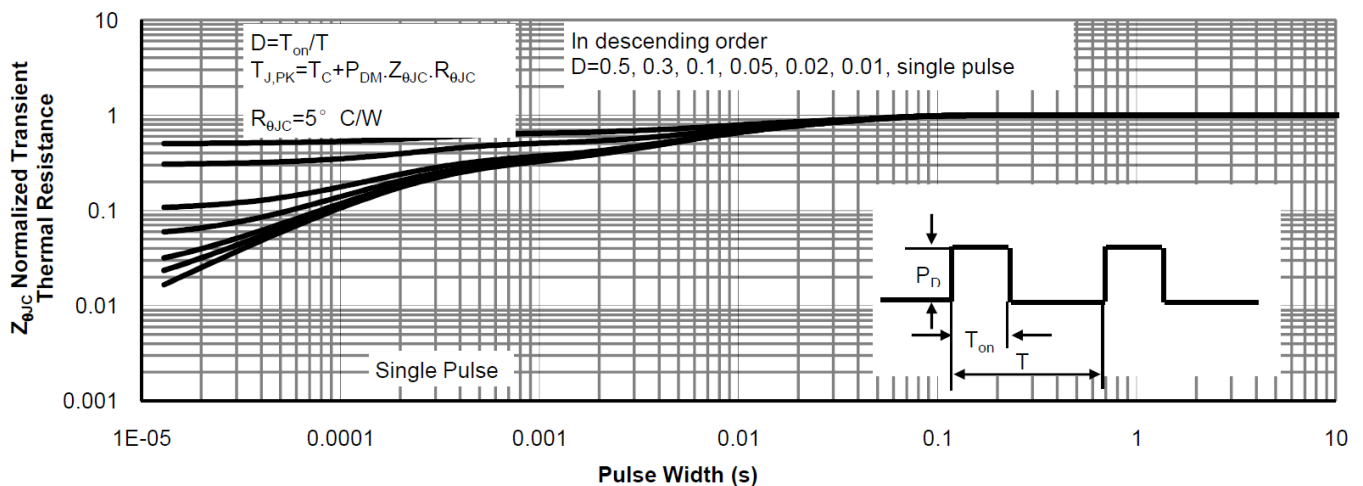
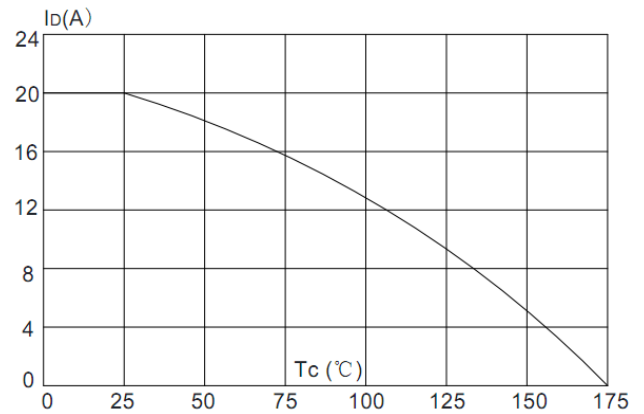
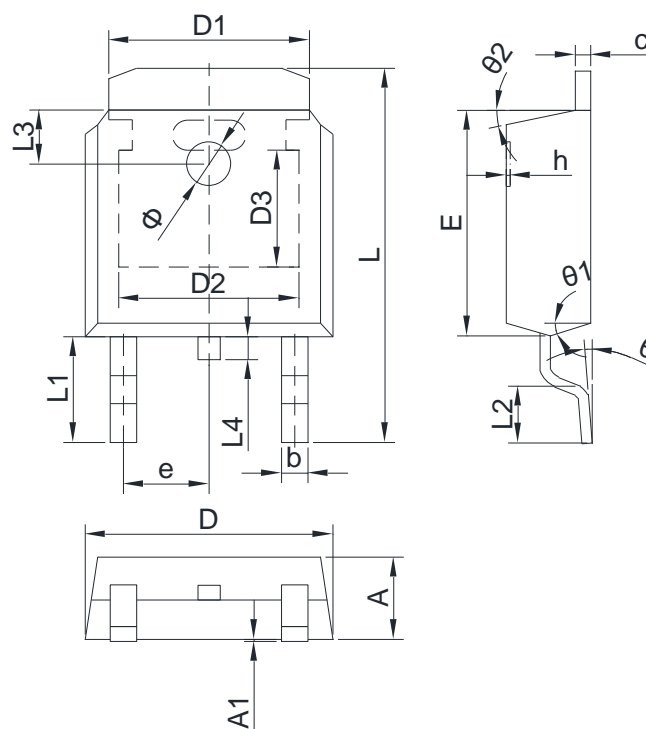


Figure 11: Normalized Maximum Transient Thermal Impedance

8. Dimension (TO-252)



SYMBOL	MILLIMETER			SYMBOL	MILLIMETER		
	MIN	Typ.	MAX		MIN	Typ.	MAX
A	2.200	2.300	2.400	h	0.000	0.100	0.200
A1	0.000		0.127	L	9.900	10.100	10.300
b	0.640	0.690	0.740	L1	2.888 REF		
C(电镀后)	0.460	0.520	0.580	L2	1.400	1.550	1.700
D	6.500	6.600	6.700	L3	1.600 REF		
D1	5.334 REF			L4	0.600	0.800	1.000
D2	4.826 REF			φ	1.100	1.200	1.300
D3	3.166 REF			θ	0°		8°
E	6.000	6.100	6.200	θ1	9° TYP		
e	2.286 TYP			θ2	9° TYP		

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